Atomic Scale Structure of Interfaces

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# Contents

**PREFACE**

MATERIALS RESEARCH SOCIETY SYMPOSIUM PROCEEDINGS  

**PART I: INITIAL STAGES OF HETEROEPITAXY**

*THEORETICAL STUDIES OF GaAs ON Si*
  John E. Northrup  
  VERY THIN 2D GaAs FILMS ON Si DURING THE EARLY STAGES OF GROWTH BY MBE

*ONSET OF GaAs HOMOEPITAXY AND HETEROEPITAXY*

**μm-SCALE LATERAL GROWTH OF Ga-MONOLAYERS OBSERVED IN-SITU BY ELECTRON MICROSCOPY**
  J. Osaka and N. Inoue  

**A LEED STUDY OF BISMUTH OVERLAYER FORMATION ON InSb(110)**
  T. Guo, K.J. Wan, and W.K. Ford  

**BISMUTH OVERLAYER FORMATION ON GaAs(110)**
  S.-L. Chang, T. Guo, W.K. Ford, A. Bowler, and E.S. Hood  

**PHOTOEMISSION CHARACTERIZATION OF THIN FILM NUCLEATION ON INERT SUBSTRATES**
  G. Haugstad, A. Raisanen, C. Caprile, X. Yu, and A. Franciosi  

**OBSERVATION OF HETEROEPITAXIALLY GROWN ORGANIC ULTRA-THIN LAYERS ON INORGANIC SUBSTRATES BY IN SITU RHEED AND BY STM**
  Masahiko Hara, Hiroyuki Sasabe, Akira Yamada, and Anthony F. Garito  

**THE INITIAL STAGES OF MBE GROWTH OF InSb ON GaAs(100) - A HIGH MISFIT HETEROINTERFACE**
  C.J. Kiely, A. Rockett, J-I. Chyi, and H. Morkoc  

**NANOLAYER REACTIONS IN ALUMINUM-METAL INTERFACES**
  E.V. Barrera, M.W. Ruckman, and S.M. Heald  

*Invited Paper*
PART II: HETEROINTERFACE STRUCTURE

*MEASUREMENT OF THE RELATIVE POSITION OF ADJACENT CRYSTALS AND THE MODELLING OF INTERFACIAL STRUCTURE
M.H.I. El-Eraki, C.J. Kiely, and R.C. Pond

HIGH-RESOLUTION IMAGING OF CoGa/GaAs AND ErAs/GaAs INTERFACES
Jane G. Zhu, Stuart McKernan, Chris J. Palmstrøm, and C. Barry Carter

PLAN-VIEW CBED STUDIES OF Ni0–ZrO2(CaO) INTERFACES
V.P. Dravid, M.R. Notis, C.E. Lyman, and A. Revcolevschi

DOUBLE CRYSTAL X-RAY DIFFRACTION MEASUREMENT OF A TRICLINICLY DISTORTED AND TILTED AlxGa1–xAs UNIT CELL PRODUCED BY GROWTH ON OFFCUT GaAs SUBSTRATES
A. Leiberich and J. Levkoff

INTERFACE STRAIN AND THE VALENCE BAND OFFSET AT THE LATTICE MATCHED In0.53Ga0.47As/InP (001) INTERFACE
Mark S. Hybertsen

ATOMIC STRUCTURE OF CaSi2/Si INTERFACES
Chris G. Van de Walle

ATOMIC STRUCTURE OF DISLOCATIONS AND INTERFACES IN SEMICONDUCTOR HETEROSTRUCTURES
A.S. Nandedkar, S. Sharan, and J. Narayan

GROWTH MODE AT THE Ge/(1102) SAPPHIRE INTERFACE
Geoffrey P. Malafsky

ORDERING AND ENERGETICS OF Hg OVERLAYERS ON Cu(001)
C.W. Hutchings, P.A. Dowben, Y.J. Kime, W. Li, M. Karimi, C. Moses, and G. Vidali

PART III: SILICIDE INTERFACE REACTIONS AND STRUCTURE

*AN INTERFACIAL PHASE TRANSFORMATION IN CoSi2/Si(111)
D.J. Eaglesham, R.T. Tung, R.L. Headrick, I.K. Robinson, and F. Schrey

ATOMIC SCALE STUDY OF CoSi/Si(111) AND CoSi2/Si(111) INTERFACES
A. Catana, M. Heintze, P.E. Schmid, and P. Stadelmann

MICROSTRUCTURAL ASPECTS OF NICKEL SILICIDE FORMATION IN EVAPORATED NICKEL-SILICON MULTILAYER THIN FILMS
Karen Holloway and Larry Clevenger

STRANSKI-KRASTANOV GROWTH OF Ni ON Si(111) AT ROOM TEMPERATURE
J.R. Butler and P.A. Bennett

*Invited Paper
X-RAY ABSORPTION STUDIES OF TITANIUM SILICIDE FORMATION
AT THE INTERFACE OF Ti DEPOSITED ON Si
D.B. Aldrich, R.W. Fiordalice, H. Jeon, Q. Islam,
R.J. Nemanich, and D.E. Sayers

ELECTRONIC AND STRUCTURAL STUDY OF Ni(Co) SILICIDE/
Si(111) CONTACT SYSTEM STUDIED BY SOFT X-RAY EMISSION
SPECTROSCOPY
H. Watabe, H. Nakamura, M. Iwami, M. Hirai, and
M. Kusaka

PART IV: OXIDE INTERFACES

IN-SITU TRANSMISSION ELECTRON MICROSCOPY STUDIES OF THE
OXIDATION OF Si(111) 7x7
J.M. Gibson

THE USE OF FRESNEL CONTRAST TO STUDY THE INITIAL STAGES
OF THE IN SITU OXIDATION OF SILICON
Frances M. Ross, J. Murray Gibson, and W.M. Stobbs

ELECTRON SPIN RESONANCE STUDIES OF SILICON DIOXIDE FILMS
ON SILICON IN INTEGRATED CIRCUITS USING SPIN DEPENDENT
RECOMBINATION
M.A. Jupina and P.M. Lenahan

AN NMR STUDY OF HYDROGEN IN SiO2 FILMS ON SILICON
David H. Levy and K.K. Gleason

ELECTRONIC STRUCTURE OF EPITAXIAL SiO2/Si(100) INTERFACES
T. Motooka

THE STRUCTURE OF INTERFACES IN OXIDE HETEROJUNCTIONS
FORMED BY CVD
Lisa A. Tietz, Scott R. Summerfelt, and
C. Barry Carter

TEMPERATURE DEPENDENT CURRENT-VOLTAGE CHARACTERISTICS
IN THIN SiO2 FILMS
Jin Zhao and N.M. Ravindra

PART V: CLEAN SURFACES AND CHEMISORBED LAYERS

*LOW ENERGY ELECTRON MICROSCOPY OF SURFACE PROCESSES ON
CLEAN Si(111) AND Si(100)
E. Bauer, M. Mundschau, W. Swiech, and W. Telieps

THE ATOMIC GEOMETRY OF THE RECONSTRUCTED (001) SURFACE
OF THE RUTILE PHASE OF SnO2
Charles B. Duke and Michael R. Thompson

A NEW DEFECT ON THE RECONSTRUCTED Si(100) SURFACE: AN
AB INITIO MOLECULAR-DYNAMICS STUDY
Sigeo Ihara, Shi Lun Ho, Tsuyoshi Uda, and
Masahiko Hirao

*Invited Paper
Si(001) MOLECULAR BEAM EPITAXY: ENHANCED DIFFUSION OR BONDING?  
S. Clarke, M.R. Wilby, and D.D. Vvedensky  

XPS ANALYSIS OF THE SAPPHIRE SURFACE AS A FUNCTION OF HIGH TEMPERATURE VACUUM ANNEALING  
E.D. Richmond  

 ADSORPTION AND TRIBOCHEMICAL REACTIONS  
W.M. Mullins and T.E. Fischer  

PART VI: SCANNING TUNNELING MICROSCOPY  
*ATOMICALLY-RESOLVED SURFACE PHOTOVOLTAGE PROBED BY OPTICALLY-EXCITED SCANNING TUNNELING MICROSCOPY  
R.J. Hamers and K. Markert  

*OBSERVATIONS OF SURFACES BY ELECTRON MICROSCOPY DURING STM OPERATION  

IMAGING BY SLIDING PLANES IN SCANNING TUNNELLING MICROSCOPY  
John D. Todd and John B. Pethica  

ROLE OF TIP MATERIAL IN SCANNING TUNNELING MICROSCOPY  
C. Julian Chen  

STM OF GOLD ON GRAPHITE  
P.A. Thomas, W.H. Lee, and R.I. Masel  

PART VII: ENCAPSULATED SURFACES  
*INTERFACIAL SUPERSTRUCTURES STUDIED BY GRAZING INCIDENCE X-RAY DIFFRACTION  
Koichi Akimoto, Jun'ichiro Mizuki, Ichiro Hirosawa, and Junji Matsui  

DIRECT OBSERVATION OF A 7x7 SUPERSTRUCTURE BURIED AT THE AMORPHOUS-Si/Si(111) INTERFACE  
Akira Sakai, Toru Tatsumi, and Koichi Ishida  

TOPOGRAPHY OF Si(111): CLEAN SURFACE PREPARATION AND SILICON MOLECULAR BEAM EPITAXY  
R.T. Tung, F. Schrey, and D.J. Eaglesham  

ELECTRONIC AND ATOMIC PROPERTIES OF a-C:H/SEMICONDUCTOR INTERFACES  
M. Wittmer, D. Ugolini, and P. Oelhafen  

NON-EQUILIBRIUM MOLECULAR DYNAMICS SIMULATION OF THE RAPID SOLIDIFICATION OF METALS  
Cliff F. Richardson and Paulette Clancy  

*Invited Paper
PART VIII: ROUGHNESS AND INTERDIFFUSION

STUDY OF INTERFACIAL SHARPNESS AND GROWTH IN (GaAs)$_m$(AlAs)$_n$ SUPERLATTICES  
D. Gammon, S. Prokes, D.S. Katzer, B.V. Shanabrook, 
M. Fatemi, W. Tseng, B. Wilkins, and H. Dietrich 339

A WEAK BEAM IMAGING TECHNIQUE FOR THE CHARACTERIZATION 
OF INTERFACIAL ROUGHNESS IN (InGa)As/GaAs STRAINED LAYER 
STRUCTURES  
J.Y. Yao, T.G. Andersson, and G.L. Dunlop 345

INTERFACIAL STABILITY AND INTERDIFFUSION EXAMINED AT THE 
ATOMIC LEVEL  
Y. Kim, A. Ourmazd, R.J. Malik, and J.A. Rentschler 351

A STUDY OF INTERFACES IN GaAs/AlAs SUPERLATTICES USING 
PHONONS  
D. Gammon, B.V. Shanabrook, S. Prokes, D.S. Katzer, 
W. Tseng, B. Wilkins, and H. Dietrich 357

IX: GRAIN BOUNDARIES AND NANOPHASE MATERIALS

STRUCTURE OF A NEAR-COINCIDENCE 29 TILT GRAIN BOUNDARY 
IN ALUMINUM  
M.J. Mills, G.J. Thomas, M.S. Daw, and F. Cosandey 365

ON THE ATOMIC STRUCTURE OF BOUNDARIES IN VERY SMALL 
METALLIC AND BIMETALLIC PARTICLES  
M. Jose-Yacaman, M. Avalos, A. Vazquez, 
S. Tehuacanero, P. Schabes, and R. Herrera 371

STRUCTURE AND PROPERTIES OF INVERSION DOMAIN BOUNDARIES 
IN 3-SiC  

ATOMISTIC SIMULATION STUDY OF INTERFACES IN NANOPHASE 
SILICON  
James A. Lupo and Michael J. Sabochick 383

THE APPLICATION OF GLANCING ANGLE EXAFS TO STUDY THE 
STRUCTURE OF PLATINUM-NICKEL MULTILAYERS  
G.M. Lamble, S.M. Heald, and B.M. Clemens 389

THE ELECTRONIC STRUCTURE OF 25 GRAIN BOUNDARIES IN Cu 
Erik C. Sowa, A. Gonis, and X.-G. Zhang 395

A MECHANISM FOR SOLUTE SEGREGATION TO GRAIN BOUNDARIES 
Chu Youyi and Zhang Sanhong 401

HIGH-RESOLUTION ELECTRON MICROSCOPY OF OLIVINE-MAGNETITE 
INTERFACES  
Stuart McKernan, C. Barry Carter, Daniel Ricoult, 
and A.G. Cullis 407

ATOMIC SCALE STRUCTURE OF TWIN BOUNDARY IN Y-Ba-Cu-O 
SUPERCONDUCTORS  
Yimei Zhu, M. Suenaga, Youwen Xu, and M. Kawasaki 413
MODELING OF NANOPHASE CONNECTIVITY IN SUBSTANCE-VOID COMPOSITE BY OBLIQUE DEPOSITION
T. Motohiro, S. Noda, A. Isogai, and O. Kamigaito 419

HIGH-RESOLUTION ELECTRON MICROSCOPY OF INTERFACES IN AlN-BRAZE METAL ALLOY SYSTEMS
A.H. Carim 425

X: NOVEL EXPERIMENTAL TECHNIQUES

NOVEL COMPACT AND HIGH-RESOLUTION ION BACKSCATTERING ANALYSIS SYSTEM, CHIRIBAS
Yoshiaki Kido, Akira Kawano, and Ichiro Konomi 433

SIMULATION AND QUANTIFICATION OF HIGH-RESOLUTION Z-CONTRAST IMAGING OF SEMICONDUCTOR INTERFACES
D.E. Jesson, S.J. Pennycook, and M.F. Chisholm 439

ATOMIC STRUCTURE AND CHEMISTRY OF Si/Ge INTERFACES DETERMINED BY Z-CONTRAST STEM
M.F. Chisholm, S.J. Pennycook, and D.E. Jesson 447

SIMULATED IMAGE MAPS FOR USE IN EXPERIMENTAL HIGH-RESOLUTION ELECTRON MICROSCOPY
Michael A. O'Keefe, Ulrich Dahmen, and Crispin J.D. Hetherington 453

SPECTROSCOPIC ELLIPSOmetry AS A NON-DESTRUCTIVE TECHNIQUE FOR CHARACTERIZATION OF ATOMIC-SCALE INTERFACES

NUMERICAL MODEL OF BOND STRENGTH MEASUREMENTS
Gerald L. Nutt 465

AUTHOR INDEX 473

SUBJECT INDEX 475

MATERIALS RESEARCH SOCIETY SYMPOSIUM PROCEEDINGS 479